(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

G00002

(43) International Publication Date
31 January 2002 (31.01.2002)

PCT

(10) International Publication Number
WO 02/009147 A3

(51) International Patent Classification[7]: H01L 21/00

(21) International Application Number: PCT/IB01/01761

(22) International Filing Date: 24 July 2001 (24.07.2001)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
60/220,883 26 July 2000 (26.07.2000) US
60/283,132 10 April 2001 (10.04.2001) US

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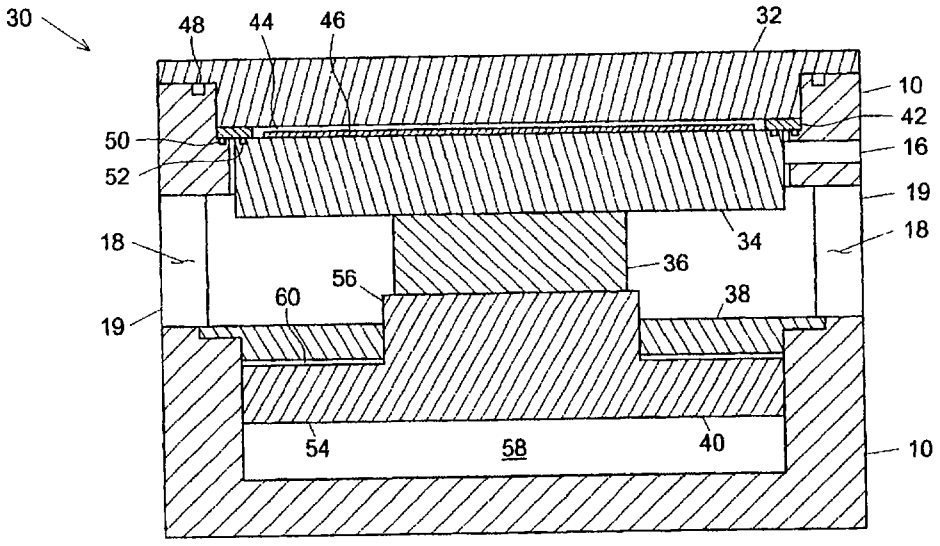
(81) Designated States *(national)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TR, TT, TZ, UA, UG, UZ, VN, YU, ZA, ZW.

(84) Designated States *(regional)*: ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:
— *with international search report*
— *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments*

[Continued on next page]

(54) Title: HIGH PRESSURE PROCESSING CHAMBER FOR SEMICONDUCTOR SUBSTRATE



(57) Abstract: A high pressure chamber comprises a chamber housing, a platen, and a mechanical drive mechanism. The chamber housing comprises a first sealing surface. The platen comprises a region for holding the semiconductor substrate and a second sealing surface. The mechanical drive mechanism couples the platen to the chamber housing. In operation, the mechanical drive mechanism separates the platen from the chamber housing for loading of the semiconductor substrate. In further operation, the mechanical drive mechanism causes the second sealing surface of the platen and the first sealing surface of the chamber housing to form a high pressure processing chamber around the semiconductor substrate.

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(88) Date of publication of the international search report:
18 July 2002

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.